

Features

- AEC-Q101 Qualified
- Split Gate Trench MOSFET Technology
- High Density Cell Design For Ultra Low RDS(on)
- Moisture Sensitivity Level 1
- Halogen Free."Green"Device^(Note1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

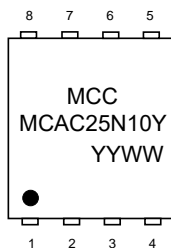
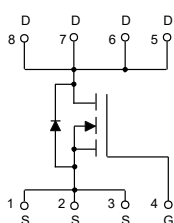
- Operating Junction Temperature Range : -55°C to +175°C
- Storage Temperature Range: -55°C to +175°C
- Thermal Resistance: 50°C/W Junction to Ambient^(Note2)
- Thermal Resistance: 2.8°C/W Junction to Case

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	I _D	T _C =25°C	25
		T _C =100°C	18
Pulsed Drain Current ^(Note 3)	I _{DM}	100	A
Total Power Dissipation ^(Note 4)	P _D	53	W
Single Pulsed Avalanche Energy ^(Note 5)	E _{AS}	25	mJ

Note:

1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-case thermal resistance.
5. T_J=25°C, V_{DD}=80V, V_{GS}=10V, R_g=25Ω, L=0.5mH.

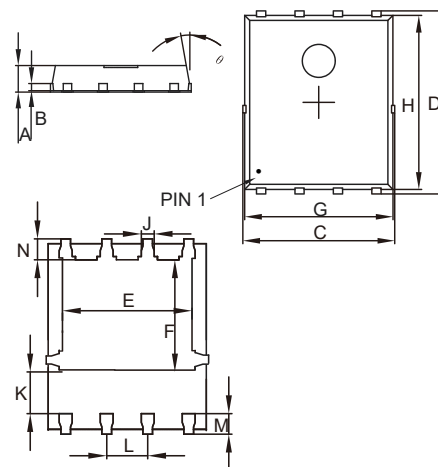
Internal Structure and Marking Code



4 codes in total
YY is the year
WW is the week

N-CHANNEL MOSFET

DFN5060



DIM	DIMENSIONS				NOTE
	INCHES		MM		
	MIN	MAX	MIN	MAX	
A	0.031	0.047	0.80	1.20	
B	0.010		0.254		TYP.
C	0.193	0.222	4.90	5.64	
D	0.232	0.250	5.90	6.35	
E	0.148	0.167	3.75	4.25	
F	0.126	0.154	3.20	3.92	
G	0.189	0.213	4.80	5.40	
H	0.222	0.239	5.65	6.06	
K	0.045	0.059	1.15	1.50	
J	0.012	0.020	0.30	0.50	
L	0.046	0.054	1.17	1.37	
M	0.012	0.028	0.30	0.71	
N	0.016	0.028	0.40	0.71	

Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=1mA$	100			V
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=80V, V_{GS}=0V$			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.7	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=25A$		25	33	m Ω
		$V_{GS}=4.5V, I_D=25A$		40	60	
Gate Resistance	R_g	f=1 MHz, Open drain		1.0		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				25	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=20A$			1.3	V
Reverse Recovery Time	t_{rr}	$I_F=15A, di_F/dt=100A/\mu s$		40		ns
Reverse Recovery Charge	Q_{rr}			67		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V, f=1MHz$		509		pF
Output Capacitance	C_{oss}			271		
Reverse Transfer Capacitance	C_{rss}			35		
Total Gate Charge	Q_g	$V_{DS}=50V, V_{GS}=10V, I_D=15A$		12.7		nC
Gate-Source Charge	Q_{gs}			2.2		
Gate-Drain Charge	Q_{gd}			5.5		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=50V, V_{GS}=10V, I_{DS}=15A, R_{GEN}=2.2\Omega$		5.2		ns
Turn-On Rise Time	t_r			7.6		
Turn-Off Delay Time	$t_{d(off)}$			18.8		
Turn-Off Fall Time	t_f			6.3		

Curve Characteristics

Fig.1 - Typical Output Characteristics

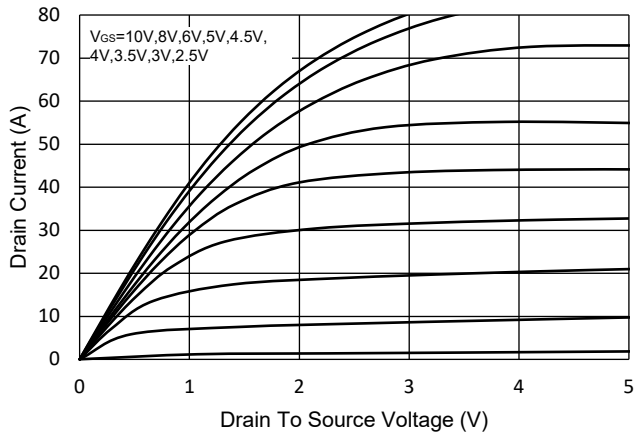


Fig.2 - Transfer Characteristic

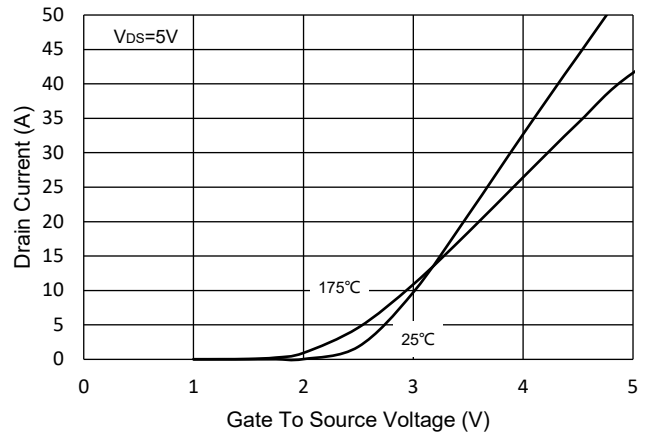


Fig.3 - $R_{DS(ON)}$ - V_{GS}

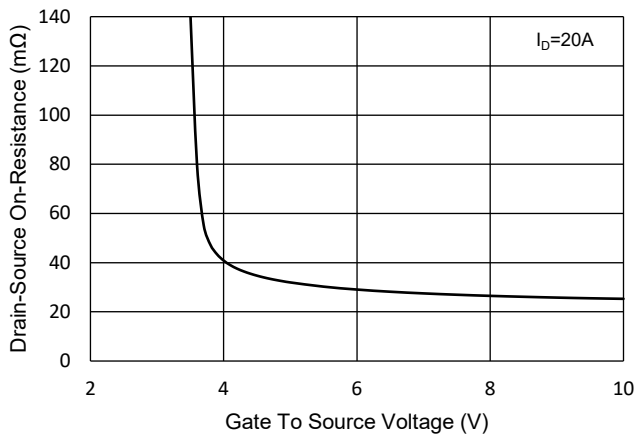


Fig.4 - $R_{DS(ON)}$ - I_D

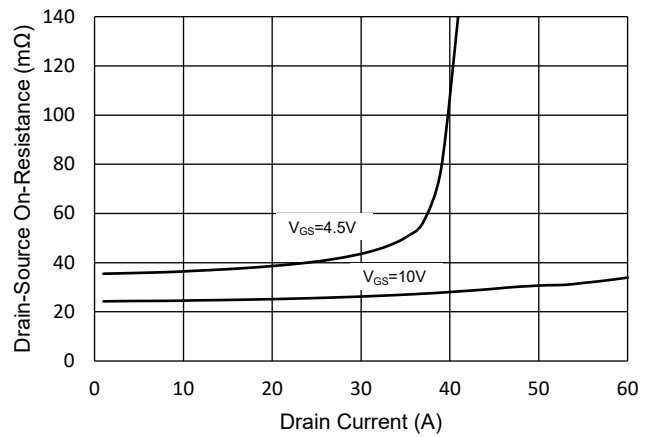


Fig.5 - Capacitance Characteristics

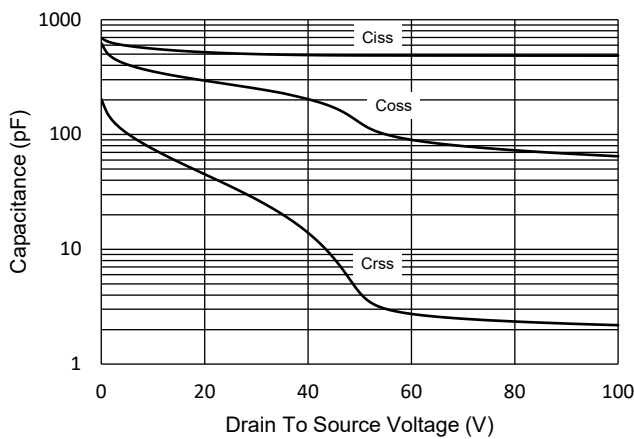
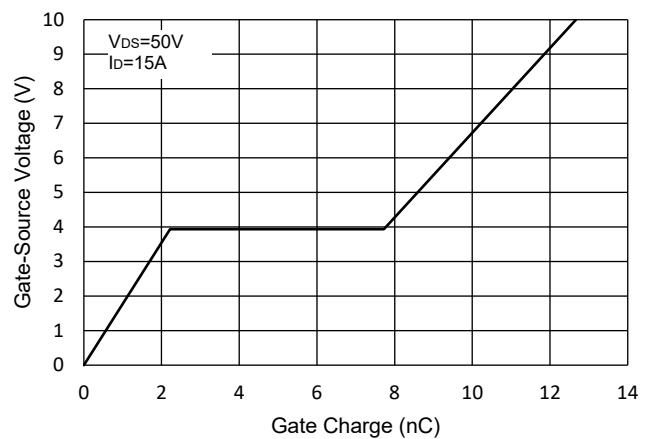


Fig.6 - Gate Charge



Curve Characteristics

Fig.7 - Normalized Threshold Voltage

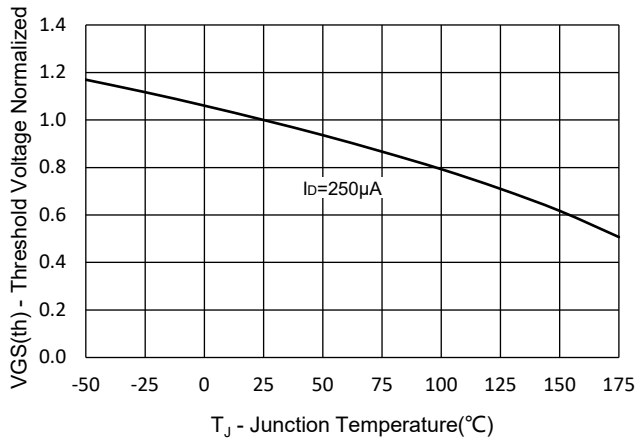


Fig.8 - Normalized On Resistance Characteristics

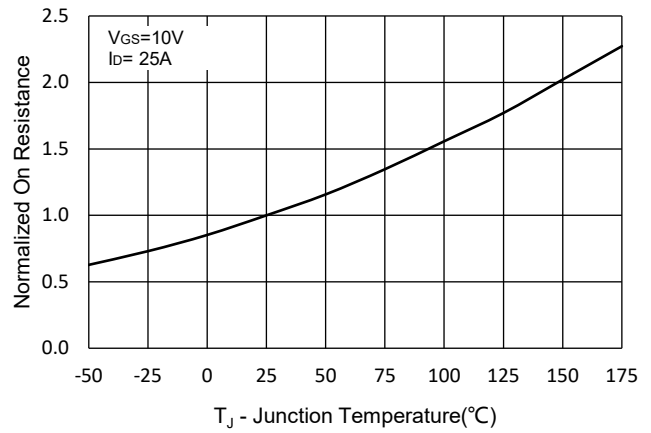


Fig.9 - I_S—V_{SD}

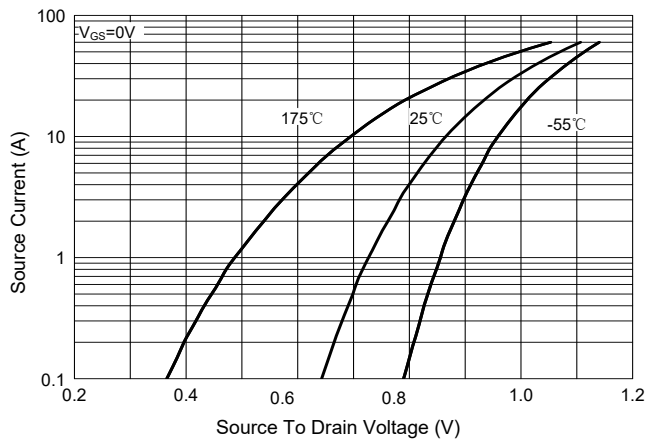


Fig.10 - Drain Current

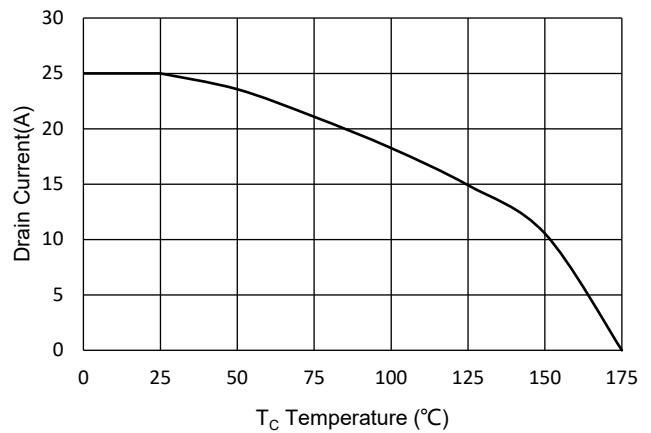
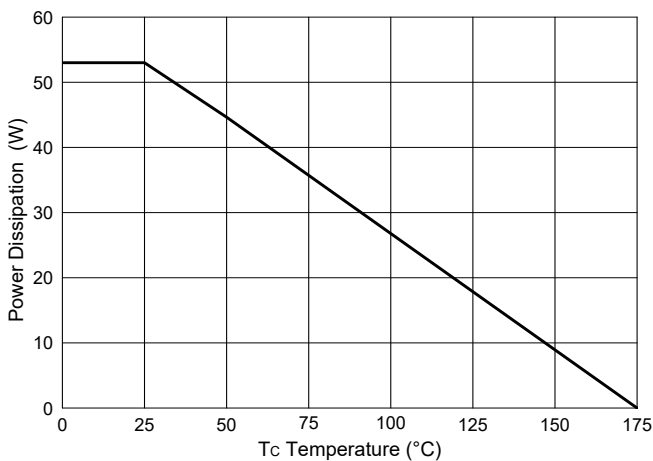


Fig.11-PD Dissipation



Curve Characteristics

Fig. 12 - Safe Operation Area

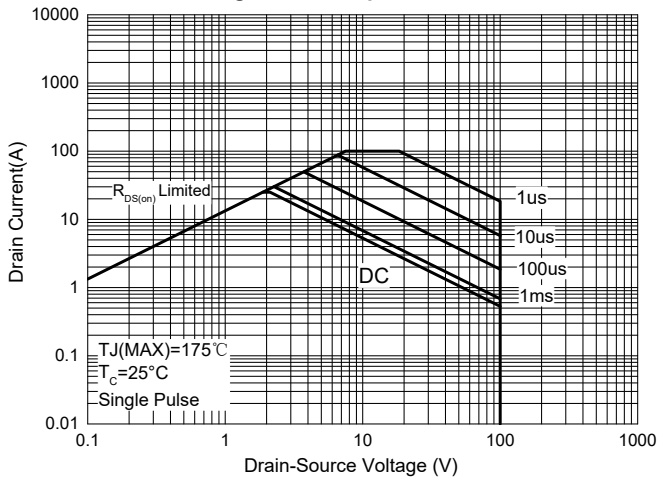
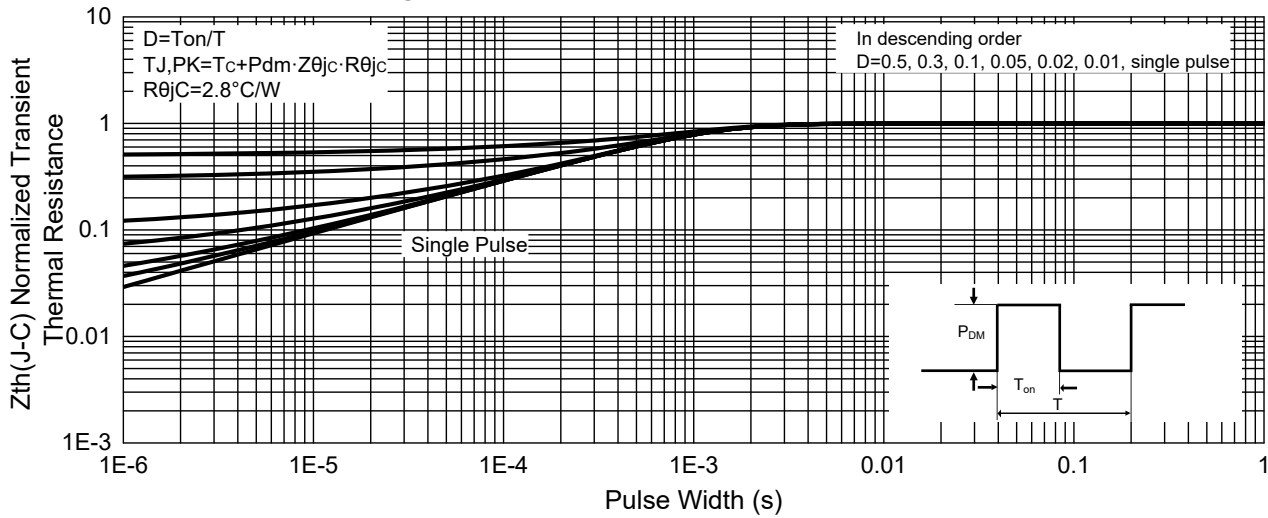


Fig. 13 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 5Kpcs/Reel

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